

■ Features

- Wide Bandgap SiC MOSFET Technology.
- Low On-Resistance with High Blocking Voltage.
- Low Capacitances with High-Speed Switching.
- Low Reverse Recovery (Qrr).
- Easy to Parallel and Simple to Drive.
- Robust against Parasitic Turn on Even 0V Turn off Gate Voltage.

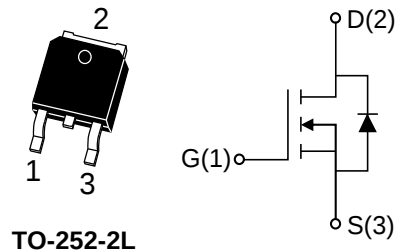
Parameter	Value	Unit
V_{DS}	750	V
$R_{DS(on)}_{typ@VGS=18V}$	100	mΩ
$I_{D@VGS=18V,TC=25^{\circ}C}$	19.2	A

■ Benefits

- Reduced Switching Losses.
- Increased System Switching Frequency.
- Increased Power Density.
- Reduction of Heat Sink Requirements.
- Reduced EMI.

■ Application

- Switch Mode Power Supplies.
- High Voltage DC/DC Converters.
- Battery Chargers.
- Motor Drives.
- Pulsed Power Applications.



Maximum ratings($T_j=25^{\circ}C$, Unless otherwise specified)

Parameter	Symbol	Test Condition	Value	Unit
Drain to Source Voltage	$V_{DS,max}$	$V_{GS}=0V, I_D=500\mu A$	750	V
Gate to Source Voltage	$V_{GS,max}$	Absolute Maximum Values	-10/+22	V
Recommended Operation Voltage of Gate to Source	$V_{GS,op}$	Recommended Operational Values	0/+18	V
Continuous Drain Current	I_D	$V_{GS}=15V, TC=25^{\circ}C$	18	A
		$V_{GS}=15V, TC=100^{\circ}C$	12.7	A
Continuous Drain Current		$V_{GS}=18V, TC=25^{\circ}C$	19.2	A
		$V_{GS}=18V, TC=100^{\circ}C$	13.6	A
Pulsed Drain Current	$I_{D(pulsed)}$	Pulse with T_p limited by T_{jmax}	55	A
Avalanche energy, Single pulse	E_{AS}	$V_{DD}=100V, L=10mH, T_j(start)=25^{\circ}C$	100	mJ
Power Dissipation	P_{tot}	$TC=25^{\circ}C, T_j=175^{\circ}C$	50	W
Operating and Storage Temperature	T_j, T_{stg}	—	-55 to +175	$^{\circ}C$
Solder Temperature, 1.6mm from case for 10s	T_L	—	260	$^{\circ}C$



Thermal Characteristics

Parameter	Symbol	Value			Unit
		Min	Typ	Max	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	—	3	—	°C/W

Electrical Characteristics

Static Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=5.2mA, T_j=25^{\circ}C$	2.6	3.5	4.6	V
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=500\mu A$	750	—	—	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=750V, T_j=25^{\circ}C$	—	—	50	μA
Gate to Source Leakage Current	I_{GSS+}	$V_{GS}=22V, V_{DS}=0V, T_j=25^{\circ}C$	—	—	250	nA
	I_{GSS-}	$V_{GS}=-10V, V_{DS}=0V, T_j=25^{\circ}C$	—	—	-250	nA
Drain to Source on Resistance	$R_{DS(on)}$	$V_{GS}=15V, I_D=12A, T_j=25^{\circ}C$	—	135	165	m Ω
		$V_{GS}=15V, I_D=12A, T_j=175^{\circ}C$	—	112	—	m Ω
		$V_{GS}=18V, I_D=12A, T_j=25^{\circ}C$	—	100	130	m Ω
		$V_{GS}=18V, I_D=12A, T_j=175^{\circ}C$	—	98	—	m Ω



Electrical Characteristics

Dynamic Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Input Capacitance	C_{iss}	VGS=0V, VDS=400V, f=100KHz, Tj=25°C	—	739	—	pF
Output Capacitance	C_{oss}		—	58	—	pF
Reverse Transfer Capacitance	C_{rss}		—	4.5	—	pF
Gate-Source Charge	Q_{gs}	VGS=0/18V, VDS=400V, ID=12A, Tj=25°C	—	14.4	—	nC
Gate-Drain Charge	Q_{gd}		—	9.7	—	nC
Total Gate Charge	Q_g		—	37.2	—	nC
Gate Resistance	R_g	VAC=25mV, f=1MHz	—	2.6	—	Ω

Switching Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Turn-On Delay Time	$t_{d(on)}$	VGS=0/18V, VDD=400V, ID=12A, Rg=5Ω, L=200uH, Tj=25°C	—	15.2	—	ns
Rise Time	t_r		—	46.8	—	ns
Turn-Off Delay Time	$t_{d(off)}$		—	22.4	—	ns
Fall Time	t_f		—	35.2	—	ns

Reverse Diode Characteristics

Parameter	Symbol	Test Condition	Value			Unit
			Min	Typ	Max	
Diode Forward Voltage	V_{SD}	VGS=0V, ISD=6A, Tj=25°C	—	4	—	V
Continuous Diode Forward Current	I_S	VGS=0V, Tj=25°C	—	28.2	—	A
Reverse Recovery Time	t_{rr}	VGS=0V, ISD=12A, VR=400V, -di/dt=1265A/us, Tj=25°C	—	13.2	—	ns
Reverse Recovery Charge	Q_{rr}		—	59.7	—	nC
Peak Reverse Recovery Current	I_{rrm}		—	7.3	—	A



Typical Performance

Fig1. Output Characteristics $T_j = -40^\circ\text{C}$

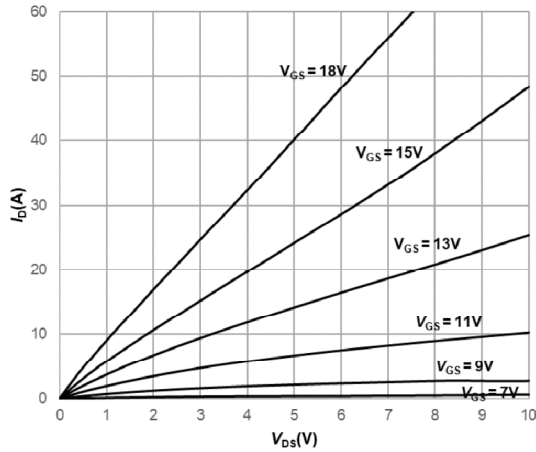


Fig2. Output Characteristics $T_j = 25^\circ\text{C}$

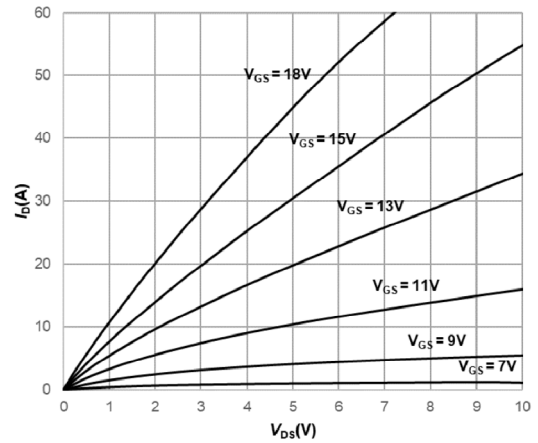


Fig3. Output Characteristics $T_j = 175^\circ\text{C}$

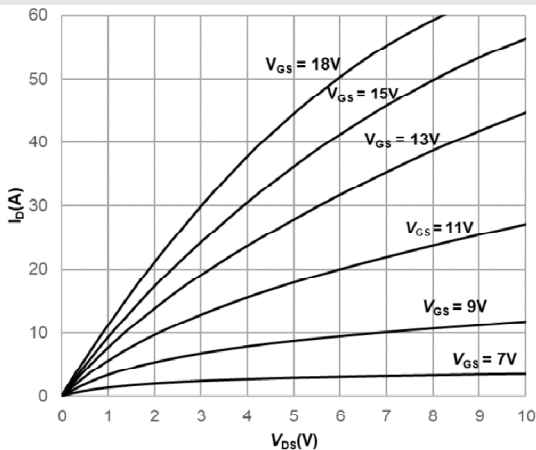


Fig4. Normalized On-Resistance vs. Temperature

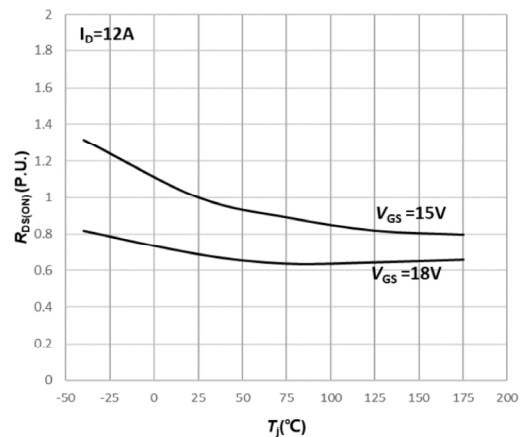


Fig5. Normalized On-Resistance vs. Drain Current For Various Gate Voltages

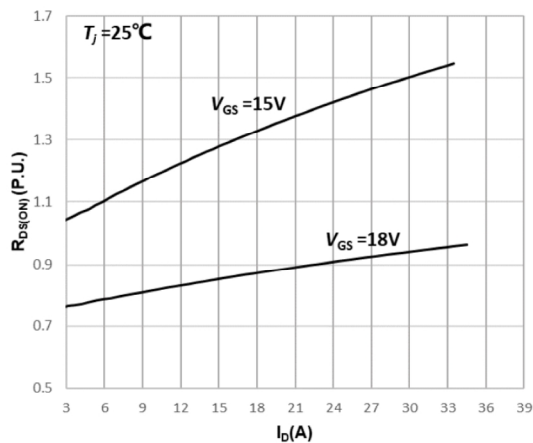
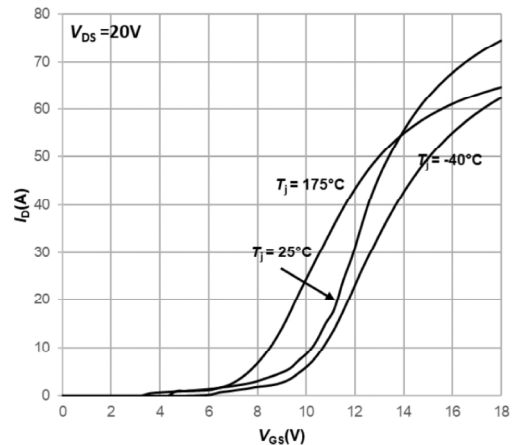


Fig6. Transfer Characteristic for Various Junction Temperature



Typical Performance

Fig7. Body Diode Characteristic at $T_j=25^\circ\text{C}$

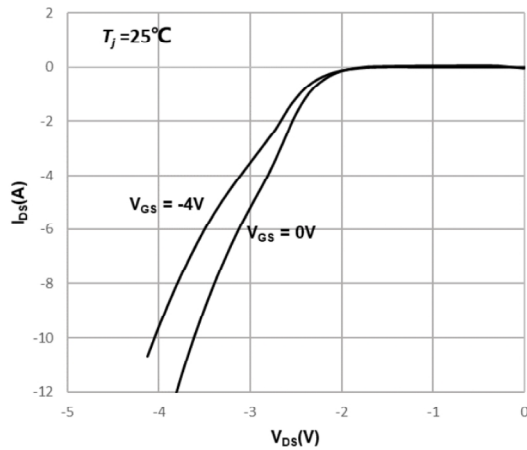


Fig8. Normalized Threshold Voltage vs. Temperature

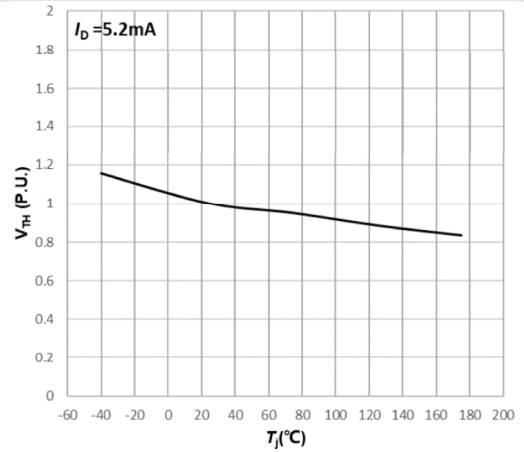


Fig9. Gate Charge Characteristics

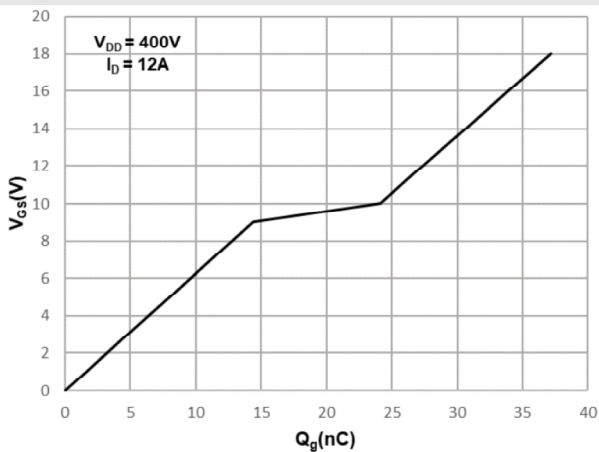


Fig10. Capacitances vs. Drain-Source Voltage(0-200V)

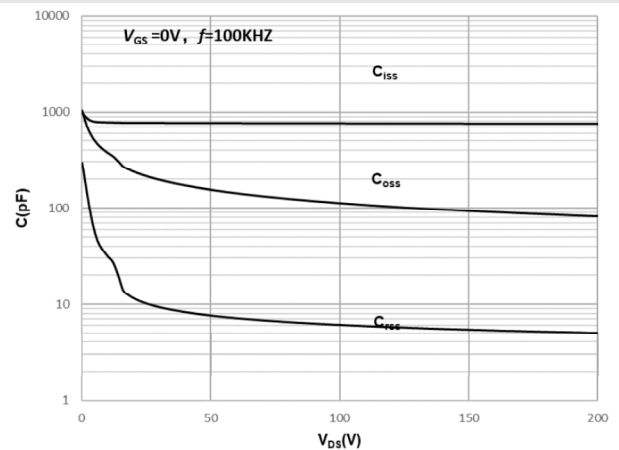


Fig11. Capacitances vs. Drain-Source Voltage(0-650V)

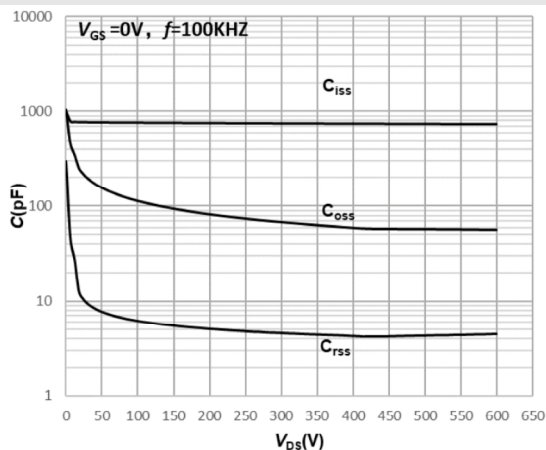
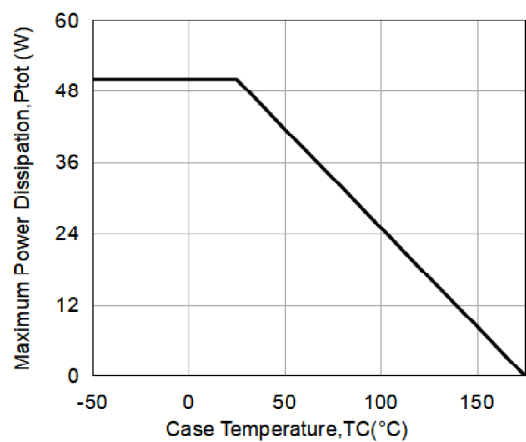
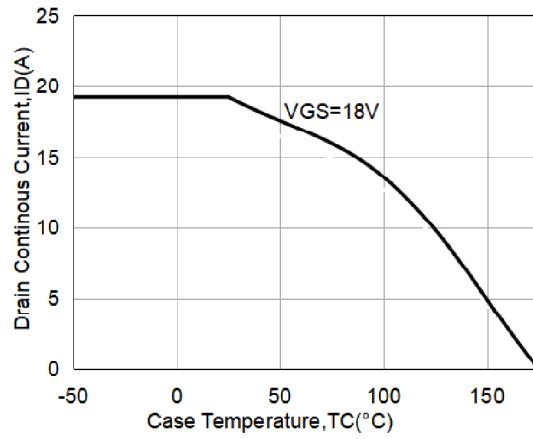


Fig12. Maximum Power Dissipation Derating vs. Case Temperature



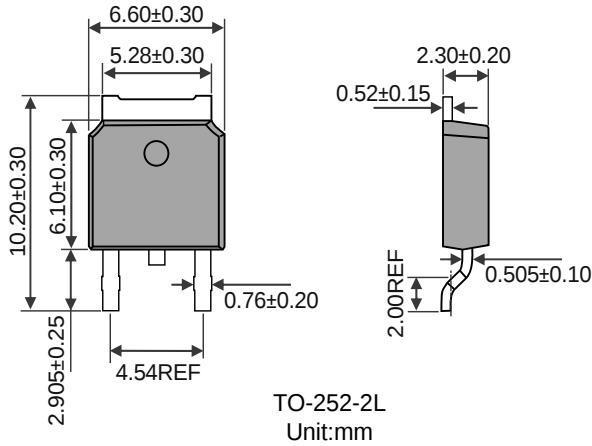
Typical Performance

Fig13. Continuous Drain Current Derating vs. Case Temperature

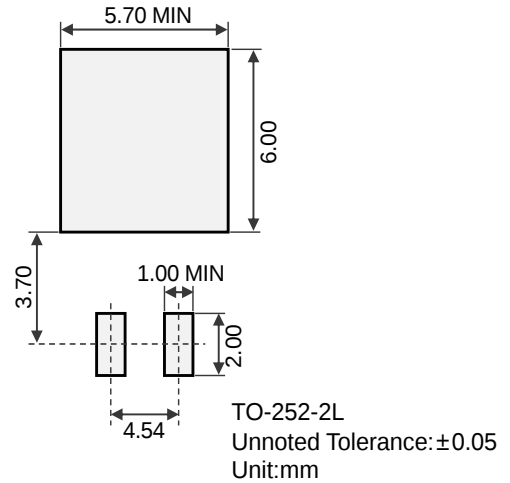


Package Outline Dimensions & Suggested Solder Pad Layout

Package Outline Dimensions



Suggested Solder Pad Layout



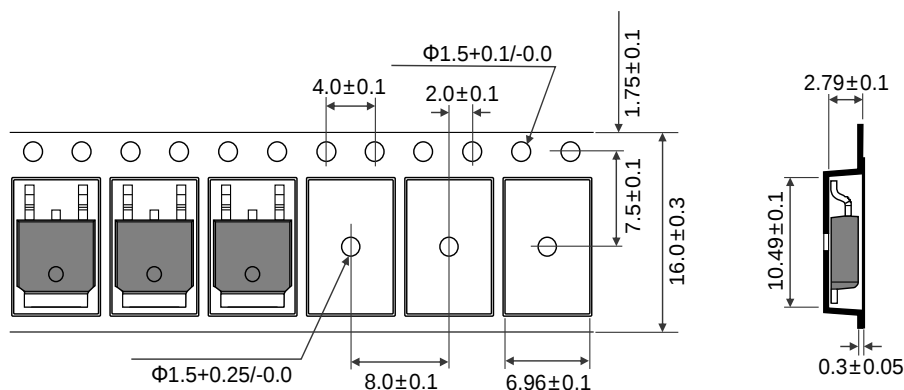
Marking Information



“MHCHXM”= Product Logo
 “Marking Code”= The Following
 “XXXX”= Date Code Marking

Marking Code	Part Number
C75N100S1	HXMC75N100S1

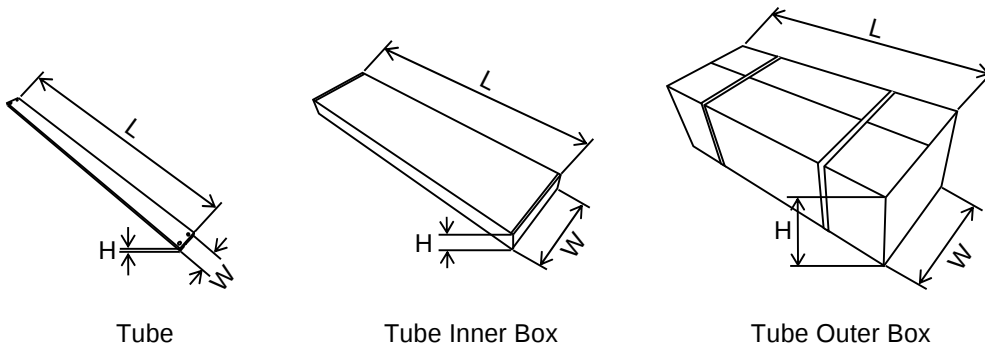
Reel Tape Dimensions (Dimensions in mm)



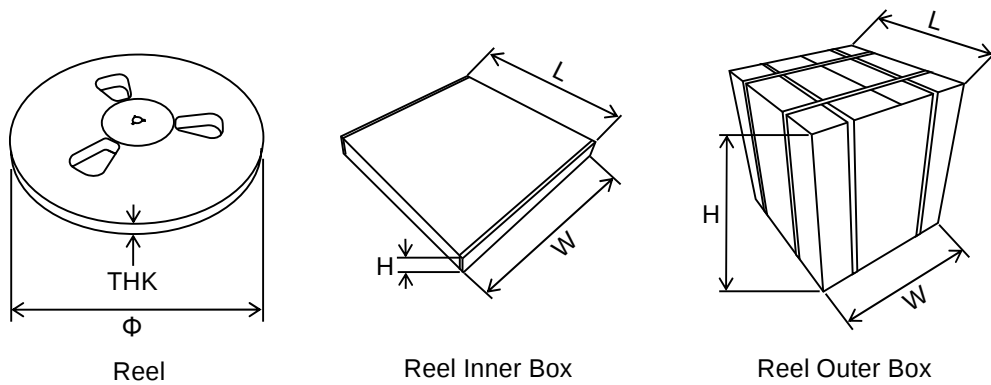
Packing Information

Packaging	Part Number	Quantity(pcs)	Size(mm)
Tube	Tube	80	L540×W20×H5
	Inner Box	4000	L570×W115×H55
	Outer Box	20000	L595×W320×H135
Reel	Reel	3000	Φ330×THK17
	Inner Box	3000	L350×W340×H25
	Outer Box	30000	L355×W300×H360

Packaging:Tube



Packaging:Reel



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